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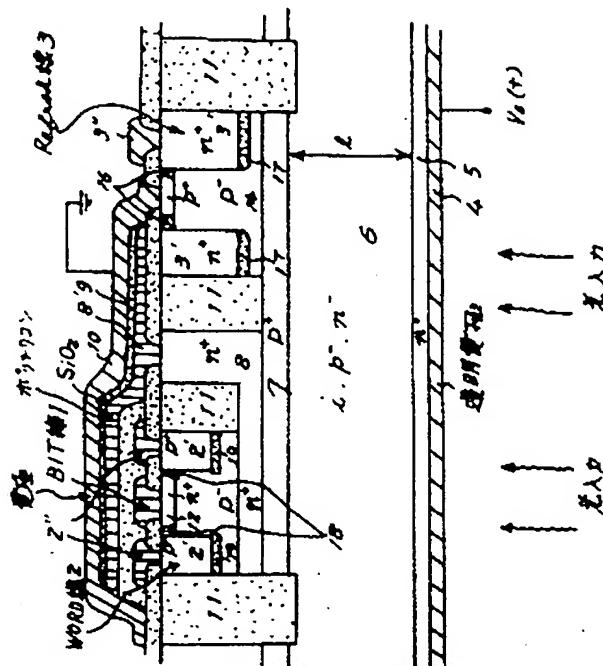
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APPLICANT : SEMICONDUCTOR RES FOUND;

INVENTOR : TAMAMUSHI NAOSHIGE;

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TITLE : SEMICONDUCTOR IMAGE PICKUP DEVICE



ABSTRACT : PURPOSE: To improve the sensitivity and the resolution of a semiconductor image pickup device as compared with both CCD and MOS image sensors by providing a plurality of cells of hook structure in which a high resistance region for substantially detecting a light and a high impurity density region having different conductivity type from the high resistance region are connected in a semiconductor substrate.

CONSTITUTION: A light input introduced through a transparent electrode 4 to which a predetermined bias voltage $V_s(+)$ is applied generates electron and hole pairs in a high resistance layer 6 specially in the vicinity of an n^+ type layer 5 of a hook structure. The layer 6 is completely depleted in the entire region by the applied voltage V_s , and an electric field to run the carrier at a saturated speed is applied to almost all the region. The generated electrons are attracted by the $V_s(+)$ bias and absorbed by the layer 5, and the holes generated in pairs are stored in a p^+ type region 7. This is because an i type region 6 is depleted by the bias voltage $V_s(+)$ and a strong electric field is applied to the entire thickness l of the i type layer. When the holes are stored in an p^+ type layer 7, the layer 7 is charged positively. Accordingly, electrons in an n^+ type region 8 override the thin layer 7 and flow to the side of the substrate.

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